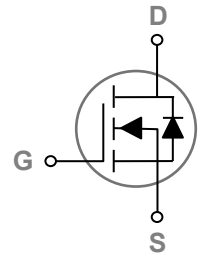


**30V N Channel MOSFETs Wafer Datasheet**
**Features**

- Die in 8" Wafer Form
- 30V , N-Channel , NGD
- $R_{DS(ON)}=7.9m\Omega$  (Max.) @


**Die Description**

Parameter	Parameter	Rating	CHIP DRAWING
Die Size (with SL)	1260 X 960	um <sup>2</sup>	
Gate Pad Size	120 X 120		
Source Pad Size	Full Metalized Source Region		
Scribe Line Size	60	um	
Wafer size	200	mm	
Wafer Thickness	4 (±0.4)	mil	
Top Metallization	4um , Al-Cu		
Back Metallization	Ti/Ni/Ag (1/3/10KÅ)		
Gate Bond Wire	2 mil Cu x 1		
Source Bond Wire	2 mil Cu x 15		
Estimated Gross Die	24,000		

**Absolute Maximum Ratings**  $T_c=25^{\circ}C$  unless otherwise noted

Symbol	Parameter	Rating	Unit
$V_{DSS}$	Drain-Source Voltage	30V	V
$V_{GSS}$	Gate-Source Voltage	±20V	V
$T_J$	Operating Junction Temperature Range	-55 to 150°C	°C
$T_{STG}$	Storage Temperature Range	-55 to 150°C	°C

**Electrical Characteristics** ( $T_J=25^{\circ}C$ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V, T_J=25^{\circ}C$	---	---	1	uA
		$V_{DS}=24V, V_{GS}=0V, T_J=125^{\circ}C$	---	---	10	uA
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=15A$	---	6.6	7.9	mΩ
		$V_{GS}=4.5V, I_D=10A$	---	9.2	12	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.5	V

Note : 1. The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$ .  
 2.  $R_{DS(ON)}$  calculated by PPAK3X3 Package